N-Channel Enhancement Mode Field Effect Transistor

Product Summary

● V_{DS}	150V
● I_D	115A
● $R_{DS(ON)}$	

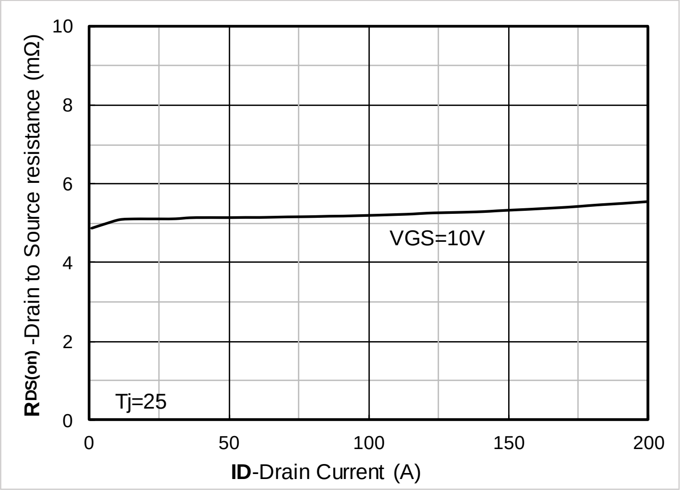

Figure 7. RDS(on) VS Drain Current

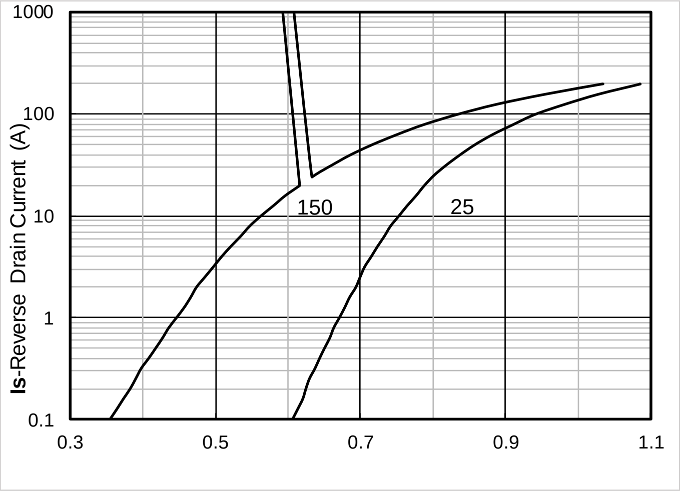

Figure 8. Forward characteristics of reverse diode

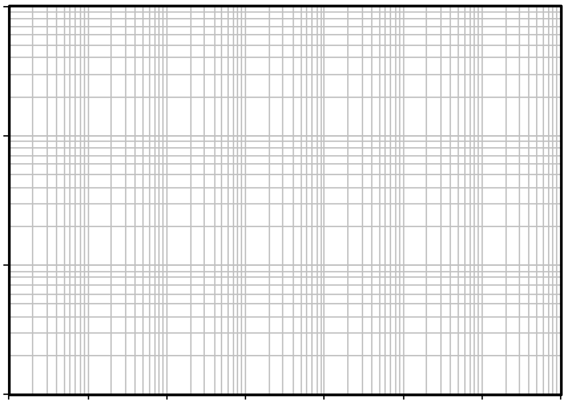

Figure 13. Maximum Transient Thermal Impedance

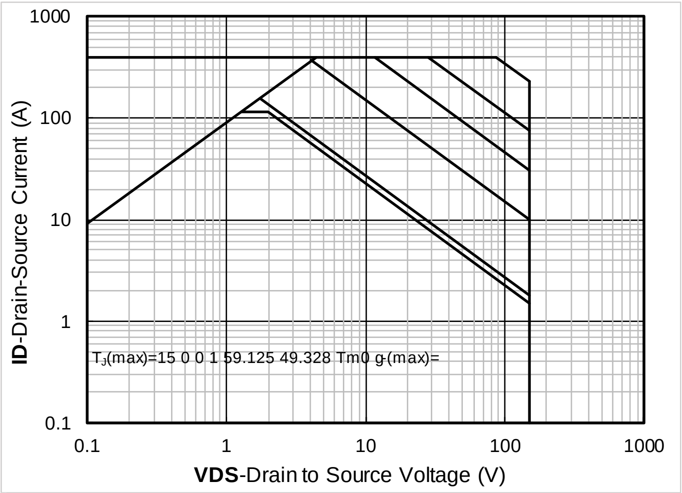

Figure 14. Safe Operation Area

■ Test Circuits & Waveforms

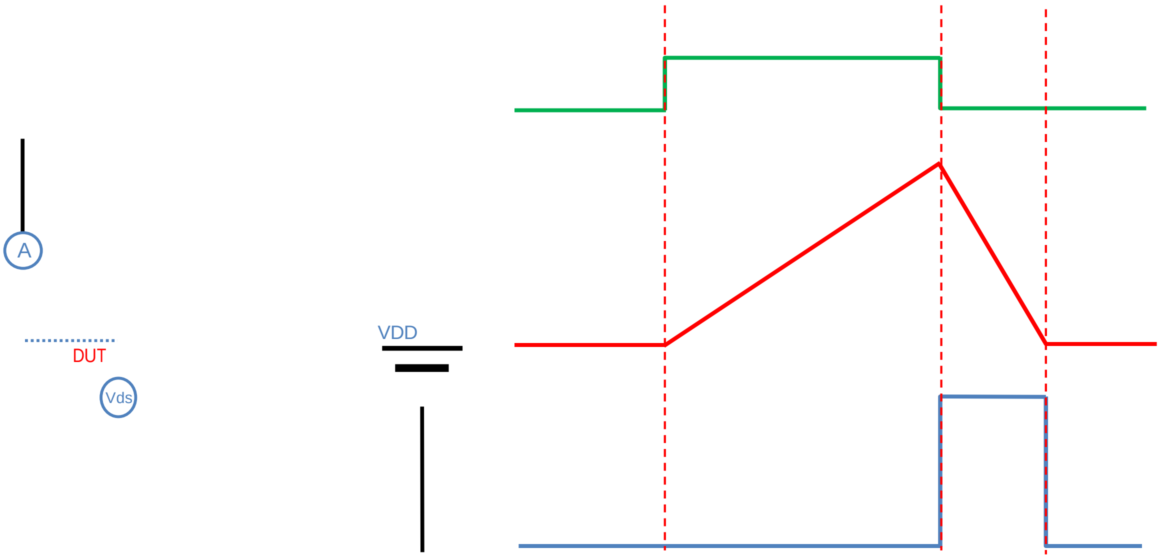

Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

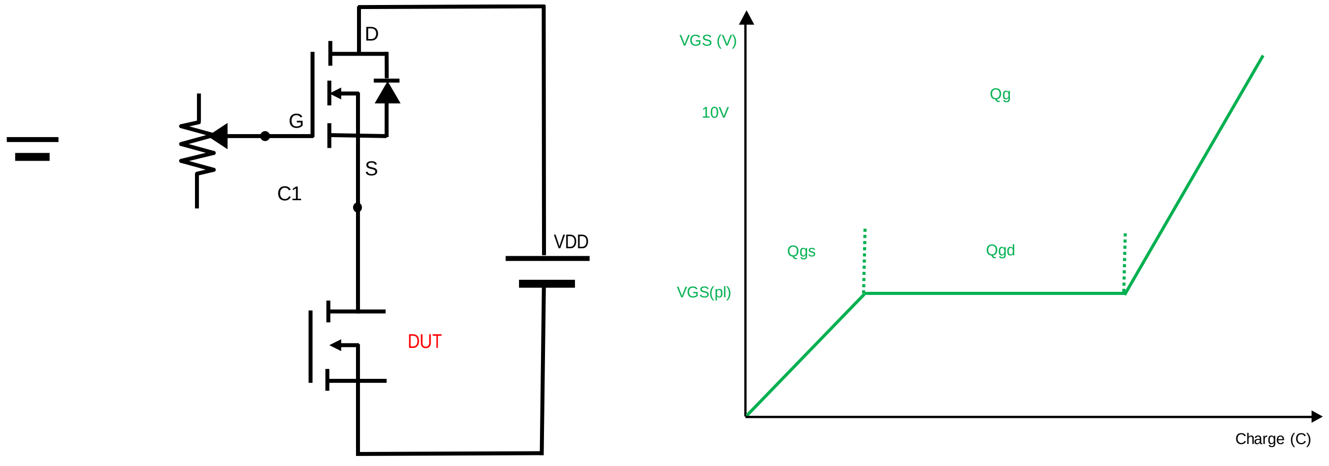

Figure B. Gate Charge Test Circuit & Waveform

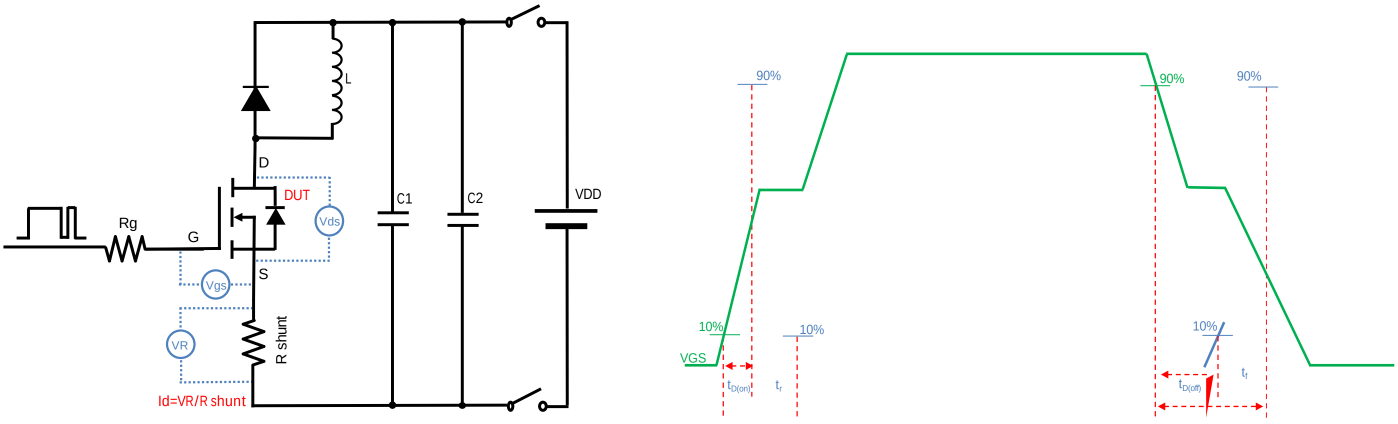

Figure C. Resistive Switching Test Circuit & Waveform

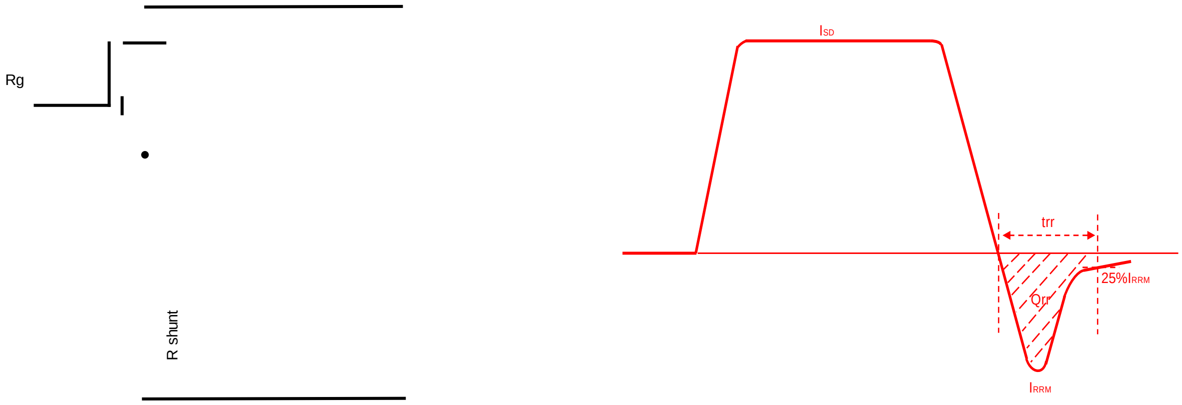

Figure D. Diode Recovery Test Circuit & Waveform

■ TO-263-HY Package information

SYM.	MIN.	
A2		
b2		0.050
c		
c2		
D2		
E		
E1		

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The product listed herein is designed to be used with ordinary electronic equipment or devices, and not designed to be used with